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November 2013

# **FQP34N20**

# N-Channel QFET<sup>®</sup> MOSFET 200 V, 31 A, 75 m $\Omega$

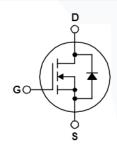
### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 31 A, 200 V,  $R_{DS(on)}$  = 75 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 15.5 A
- · Low Gate Charge (Typ. 60 nC)
- · Low Crss (Typ. 55 pF)
- · 100% Avalanche Tested





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP34N20	Unit
V <sub>DSS</sub>	Drain-Source Voltage		200	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C	C)	31	A
	- Continuous (T <sub>C</sub> = 100°	°C)	20	A
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	124	А
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	640	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	31	А
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		180	W
	- Derate above 25°C		1.43	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Rang	ge	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering 1/8" from Case for 5 seconds	g,	300	°C

# **Thermal Characteristics**

Symbol	Parameter	FQP34N20	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP34N20	FQP34N20	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics	T <sub>C</sub> = 25°C unless otherwise noted.
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	nracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	200			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.2		V/°C
I <sub>DSS</sub>	Zoro Coto Voltogo Droin Current	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V			1	μА
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 160 V, T <sub>C</sub> = 125°C			10	μА
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nΑ
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA

#### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15.5 A		0.06	0.075	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 15.5 A		25		S

# **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,	 2400	3100	pF
Coss	Output Capacitance	f = 1.0 MHz	 430	560	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		 55	70	pF

# **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 100 V, I <sub>D</sub> = 34 A,		40	90	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		280	570	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	. 1.0		125	260	ns
t <sub>f</sub>	Turn-Off Fall Time		/	115	240	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 160 V, I <sub>D</sub> = 34 A,		60	78	nC
Q <sub>g</sub> Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		17		nC
$Q_{gd}$	Gate-Drain Charge			27		nC

# **Drain-Source Diode Characteristics and Maximum Ratings**

Is	Maximum Continuous Drain-Source Diode Forward Current		 	31	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		 	124	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 31 A	 /	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 34 A,	 150		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs	 0.95		μС

- Notes: 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 1.0 mH,  $I_{AS}$  = 31 A,  $V_{DD}$  = 50 V,  $R_{G}$  = 25  $\Omega$ , starting  $T_{J}$  = 25°C. 3.  $I_{SD}$  ≤ 34 A, di/dt ≤ 300 A/ $\mu$ s,  $V_{DD}$  ≤ BV<sub>DSS</sub>, starting  $T_{J}$  = 25°C. 4. Essentially independent of operating temperature.

# **Typical Characteristics**

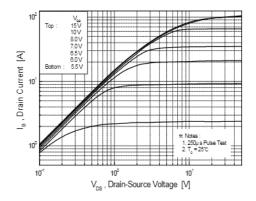


Figure 1. On-Region Characteristics

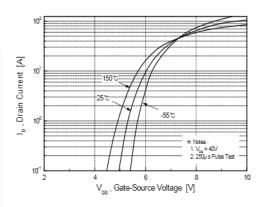


Figure 2. Transfer Characteristics

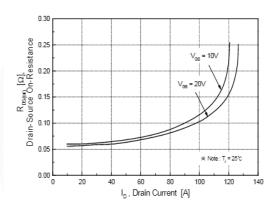


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

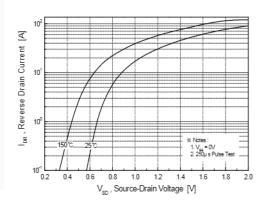


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

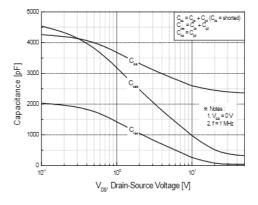


Figure 5. Capacitance Characteristics

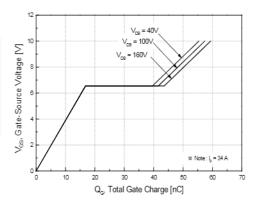


Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)

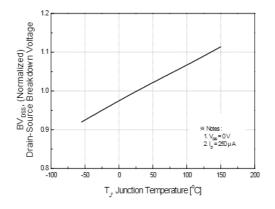
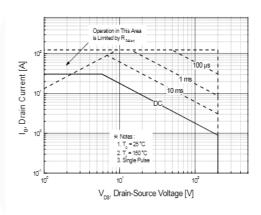


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



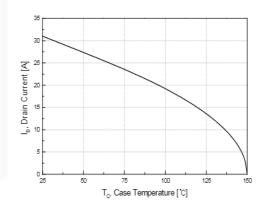


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

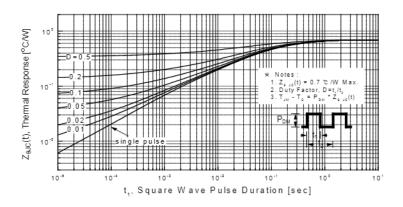


Figure 11. Transient Thermal Response Curve

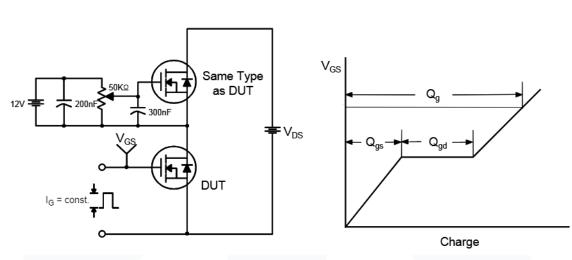


Figure 12. Gate Charge Test Circuit & Waveform

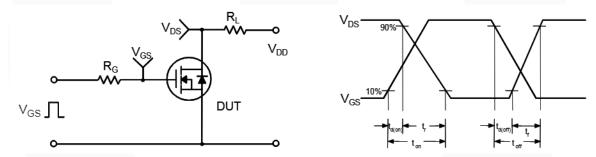


Figure 13. Resistive Switching Test Circuit & Waveforms

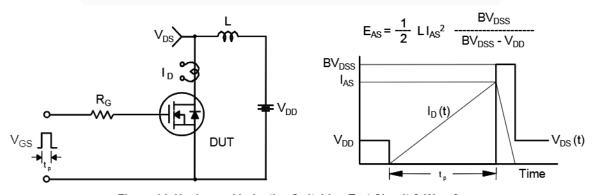
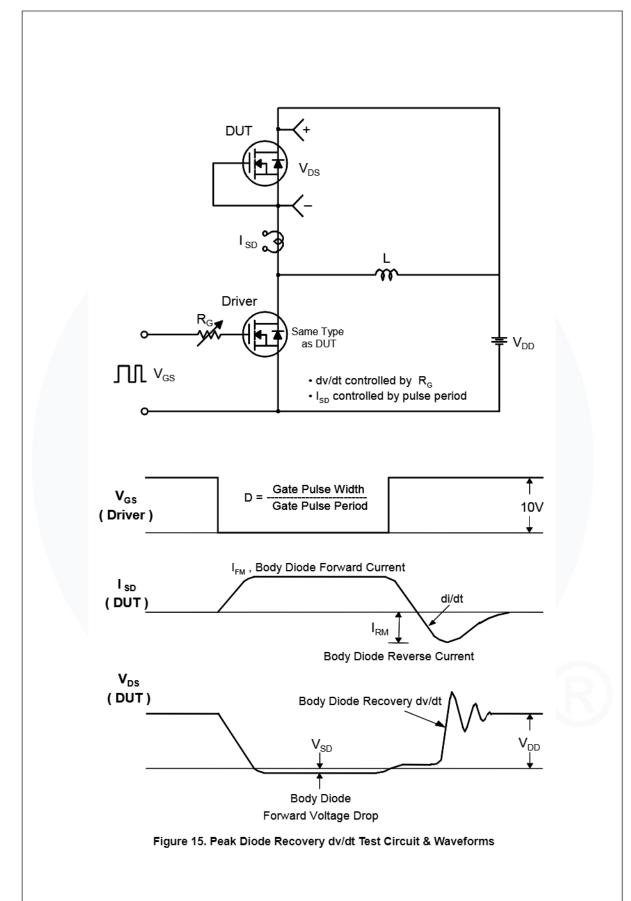


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

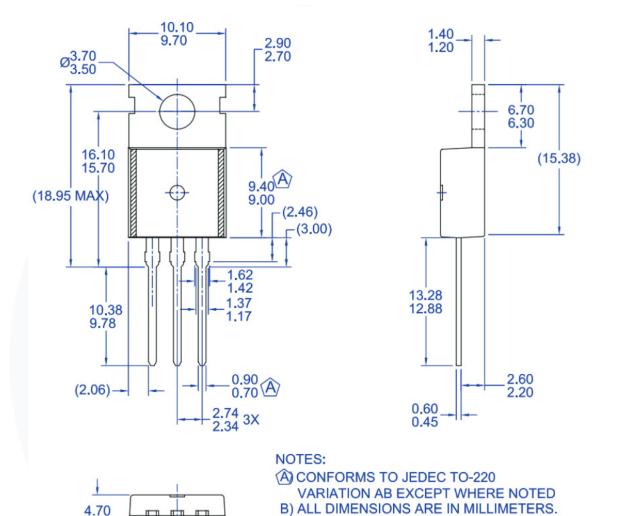


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

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